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New Galvanomagnetic Effects of Polycrystalline Magnetic Films

Y. Zhang,[1,2] H. W. Zhang,[3] and X. R. Wang[1,2,*]

[1]*Physics Department, The Hong Kong University of Science and Technology, Clear Water Bay, Kowloon, Hong Kong*
[2]*HKUST Shenzhen Research Institute, Shenzhen 518057, China*
[3]*School of Microelectronics and Solid-State Electronics, University of Electronic Science and Technology of China, Chengdu, Sichuan 610054, China*

Within the linear response of polycrystalline magnetic films to electric currents, a general analysis predicts three new galvanomagnetic effects originated from the two-dimensional nature of the films. These new galvanomagnetic effects, which differ from the conventional extraordinary Hall effect and anisotropic magnetoresistance, are follows. 1) The longitudinal resistivity depends linearly on the magnetization component perpendicular to a film. 2) A current parallel to the magnetization can generate an electric field in the vertical direction of a film. 3) A current perpendicular to a film can generate an electric field along the magnetization direction.

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The galvanomagnetic effects are a well-studied subject in condensed matter physics [1–3]. The subject is about the generation of electric field in a metal or a semiconductors by an electric current. These effects are often used to probe the electronic properties of matter. The galvanomagnetic effects include many well-known phenomena such as classical and quantum Hall effect [4], extraordinary Hall effect (EHE) [5–8], anisotropic magnetoresistance (AMR) [9, 10], and de Haas-Schubnikov oscillations [11], as well as recently discovered spin Hall and inverse spin Hall effect [12–16]. Within the linear response region, the theories of galvanomagnetic effects are well-developed. For example, one can use the Kubo formula [17] or Boltzmann theory to compute resistivity tensor of a given microscopic model in the presence or absence of a magnetic field. One can also use semiclassical dynamical equations for quasi-electrons or holes to obtain a current density under given external driven forces. Although these theories can be used to compute the transport properties of a given microscopic model, the microscopic mechanism of one particular galvanomagnetic effect may not be as transparent as one might think. For example, the origins of the EHE were completely known only in recent years [8]. A microscopic understanding of AMR is still a research subject. So far, most of the well-known galvanomagnetic effects were first found in experiments instead of being predicted by theories. In this letter, new galvanomagnetic effects for polycrystalline magnetic films are predicted. Our predictions are based on the general requirement that all physical quantities must be tensors such as scalars (tensors of rank 0) and vectors (tensors of rank 1), and all physics equations can be written in tensor forms. Our analysis shows that all possible galvanomagnetic effects for polycrystalline magnetic bulks are already known. However, three new galvanomagnetic effects, which are not known to the best of our knowledge, exist in polycrystalline magnetic films due to their two dimensional nature.

Consider a piece of ferromagnetic metal with a current density $\mathbf{J}$ passing through it. The galvanomagnetic effects of the system in the linear response region is best described by the generalized Ohm's law. The well-known generalized Ohm's law of polycrystalline ferromagnetic metals is [18–20]

$$\mathbf{E} = \rho_\perp \mathbf{J} + \frac{\Delta\rho}{M^2}(\mathbf{J}\cdot\mathbf{M})\mathbf{M} - R_0\mathbf{J}\times\mathbf{H} - R_1\mathbf{J}\times\mathbf{M}, \quad (1)$$

where M is the magnitude of magnetization $\mathbf{M}$ and $\mathbf{H}$ is an applied external magnetic field. $\mathbf{E}$ is the electric field induced by the current density $\mathbf{J}$. $\rho_\perp$ is the resistivity when $\mathbf{M}$ and $\mathbf{J}$ are perpendicular with each other. $\Delta\rho = \rho_{||} - \rho_\perp$ is the difference between $\rho_\perp$ and the resistivity $\rho_{||}$ when $\mathbf{M}$ is parallel to $\mathbf{J}$. This term is usually called the AMR. This AMR gives the famous universal angular dependence of longitudinal resistance (resistivity) $\rho_{xx} = \rho_\perp + \Delta\rho\cos^2\theta$, where θ is the angle between $\mathbf{M}$ and $\mathbf{J}$. R_0 and R_1 are the ordinary and extraordinary Hall coefficients. This generalized Ohm's law is the basis of the electrical detection of ferromagnetic resonance [16, 18–20].

Eq. (1) is in fact the most general linear response of a polycrystalline magnet. It could be understood by the following reasoning. For simplicity, let us assume that there is no external magnetic field and $\mathbf{M}$ is the only vector variable available in the system [21]. For the linear response of the system to a current density $\mathbf{J}$, the most general expression of the induced electric field must be $\mathbf{E} = \overleftrightarrow{\rho}(\mathbf{M})\mathbf{J}$, where $\overleftrightarrow{\rho}(\mathbf{M})$ is a rank-2 Cartesian tensor, depending on $\mathbf{M}$. It is well-known that a Cartesian tensor of rank 2 can be decomposed into the direct sum of a scalar of function of M, a vector that is a function of M multiplying $\mathbf{M}$, and a traceless symmetric tensor that is a function of M multiplying $\mathbf{MM} - M^2/3$. Thus the most general expression of $\mathbf{E}$ is

$$\mathbf{E} = \big(\rho_\perp + \frac{\Delta\rho}{3}\big)\mathbf{J} + R_1\mathbf{M}\times\mathbf{J} + \frac{\Delta\rho}{M^2}\big(\mathbf{MM} - \frac{M^2}{3}\big)\cdot\mathbf{J}. \quad (2)$$

This is exactly Eq. (1). Although no new physics is obtained from this reasoning, this analysis is capable of

finding all galvanomagnetic effects for the bulk of polycrystalline magnets. Interestingly, a similar spirit, but with a much more tedious and lengthy argument, was used before to obtain the AMR [22].

Encouraged by the above success, we carry out a similar analysis for polycrystalline magnetic films, lying in the xy-plane as shown in Fig. 1. Although a polycrystalline film is isotropic in the film plane, $\hat{z}$ is an available vector and $\overleftrightarrow{\rho}(\mathbf{M},\hat{z})$ should be a function of both $\mathbf{M}$ and $\hat{z}$. Of course, the sense of the positive z-direction must be determined by the current density and the in-plane component of the magnetization [23]. Since three vectors ($\mathbf{M}$, $\hat{z}$, and $\mathbf{M}\times\hat{z}$) and three traceless symmetric tensors ($\mathbf{MM}-M^2/3$, $\mathbf{M}\hat{z}+\hat{z}\mathbf{M}-2M_z/3$, and $\hat{z}\hat{z}-1/3$) can be constructed out of $\mathbf{M}$ and $\hat{z}$, we have, with a similar reasoning as that for a bulk polycrystalline magnet,

$$\begin{aligned}\mathbf{E} &= \big(\rho_\perp+\frac{\Delta\rho+\rho_2}{3}\big)\mathbf{J}+\big(R_1\mathbf{M}+\\ &\rho_1\hat{z}+R_2'\mathbf{M}\times\hat{z}\big)\times\mathbf{J}+\Big[\frac{\Delta\rho}{M^2}\big(\mathbf{MM}-\frac{M^2}{3}\big)+\\ &R_3'\big(\mathbf{M}\hat{z}+\hat{z}\mathbf{M}-2\frac{M_z}{3}\big)+\rho_2\big(\hat{z}\hat{z}-\frac{1}{3}\big)\Big]\cdot\mathbf{J}=\\ &\rho_\perp\mathbf{J}-R_1\mathbf{J}\times\mathbf{M}+\frac{\Delta\rho}{M^2}\big(\mathbf{M}\cdot\mathbf{J}\big)\mathbf{M}-\rho_1\mathbf{J}\times\hat{z}+\\ &R_2J_z\mathbf{M}+R_3\big(\mathbf{M}\cdot\mathbf{J}\big)\hat{z}-R_4M_z\mathbf{J}+\rho_2J_z\hat{z},\end{aligned}\tag{3}$$

where $R_2\equiv R_2'+R_3'$, $R_3\equiv R_3'-R_2'$ and $R_4\equiv(2/3)R_2'$. The ρ_1-term may be interpreted as the spin-Hall term if the sign of ρ_1 for spin-up electrons is opposite to that for spin-down electrons. Microscopically, it is known that spin-orbit interaction can lead to a term like this [12, 13]. Obviously, ρ_2 is the resistivity along the $z-$direction. Interestingly, one obtains three new terms. R_2-term says that a current perpendicular to the film induces an electric field in $\mathbf{M}$ direction. R_3-term says that a current along $\mathbf{M}$ direction generates an electric field in the $z-$direction. R_4-term says that the longitudinal resistivity of the film depends on M_z linearly. Since the sense of the positive $z-$direction is lost when the in-plane components of $\mathbf{M}$ and $\mathbf{J}$ are parallel to each other, one should expect $R_4=0$ when $\mathbf{J}$ is in-plane. In general, $R_4\neq 0$, and the longitudinal resistivity of a polycrystalline film changes when the current reverses its direction so $+\hat{z}$ becomes $-\hat{z}$. This is the fingerprint feature of this term. It destroys the symmetry of $\mathbf{E}(\mathbf{M},-\mathbf{J})=-\mathbf{E}(\mathbf{M},\mathbf{J})$ that Eq. (1) posses. Like a semiconductor diode, this term leads to rectification effect. It should be pointed out that all the coefficients of these terms depend, in principle, on M as well as other possible variables or parameters like the temperature and impurities (that will not change our tensor analysis). Generally speaking, all these new terms should exist. Of course, their values depend on microscopic interactions that lead to these terms.

In order to find out how to experimentally verify the new effects, let us examine two experimental configurations involving a polycrystalline magnetic film as schematically shown in Fig. 1. Fig. 1(a) is the case that a current density flows in the film, say $\mathbf{J}=J\hat{x}$, while Fig. 1(b) corresponds to a current perpendicular to the film, $\mathbf{J}=J\hat{z}$. In the case of Fig. 1(a), electric field $\mathbf{E}$ in the $x-$, $y-$ and $z-$directions are proportional to ρ_{xx}, ρ_{yx} and ρ_{zx}. According to Eq. (3), $\rho_{xx}=\rho_\perp+(\Delta\rho/M^2)M_x^2-R_4M_z$. The first two terms describe the AMR. The third term says that the longitudinal resistance has an additional contribution linear in M_z. This contribution vanishes when $\mathbf{M}$ lies in-plane of the magnetic film. All terms in ρ_{yx}, $\rho_{yx}=(\Delta\rho/M^2)M_xM_y+\rho_1+R_1M_z$, are known before (AMR, EHE and SHE). However, $\rho_{zx}=(\Delta\rho/M^2)M_xM_z-R_1M_y+R_3M_x$ depends on R_3. For an in-plane magnetized film, $\rho_{zx}=-R_1M_y+R_3M_x$, so that the fingerprint of the new terms is $R_3M\cos(\theta)$ behavior, where θ is the angle between $\mathbf{M}$ and $\mathbf{J}$. Unfortunately, the film thickness cannot be too large since Eq. (3) is for a two-dimensional film. A reasonable length scale is electron mean-free path that is order of nanometers to microns for most metals at normal conditions. On the other hand, the way to measure a resistivity is to convert it to a voltage signal. From this consideration, ρ_{zx} is not a good quantity to measure because one expects voltage signal in vertical direction induced by an in-plane current would be too small to measure for a micron thick film. Nevertheless, one can use this configuration to measure R_4 by using a single domain thin film so that the voltage signal would not be averaged out. To simplify the analysis, it is better to keep $\mathbf{M}$ in the yz-plane as illustrate in Fig. 1(a). In this configuration, $\rho_{xx}=\rho_\perp-R_4M_z$. Reverse the current direction, one has $\rho_{xx}=\rho_\perp+R_4M_z$. Thus the difference in voltage drop for the two opposite current directions is proportional to R_4. One can also study M_z-dependence of the voltage drop in the $x-$direction at a fixed $\mathbf{J}$. One may use an external magnetic field to tune M_z.

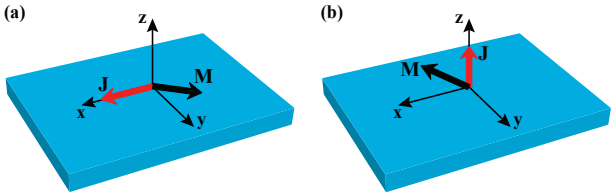

FIG. 1: (Color online) Schematic illustration of two possible experimental configurations of a polycrystalline magnetic film lying in the $xy-$plane. The z-axis is perpendicular to the film. (a) Current density $\mathbf{J}$ flows along the x-direction in the magnetic film. The magnetization $\mathbf{M}$ is in the $yz-$plane. (b) Current density $\mathbf{J}$ flows along the z-direction. The magnetization $\mathbf{M}$ is in the $xz-$plane.

In the case of Fig. 1(b) and if one chooses $x-$axis parallel to the in-plane component of $\mathbf{M}$ ($M_y=0$), then the $x-$, $y-$ and $z-$components of $\mathbf{E}$ are proportional to ρ_{xz}, ρ_{yz} and ρ_{zz}. This may be detected by measuring the voltage drops in the $x-$, $y-$, and $z-$directions when a

tunneling current is passing through a multilayer sample in which a thin single domain magnetic layer is sandwiched between two non-magnetic layers. According to Eq. (3), $\rho_{xz} = (\Delta\rho/M^2)M_xM_z + R_2M_x$, $\rho_{yz} = -R_1M_x$ and $\rho_{zz} = (\rho_\perp + \rho_2) + (\Delta\rho/M^2)M_z^2 + (R_2 + R_3 - R_4)M_z$. Obviously, the voltage drop in the $x-$direction reverses its sign when $\mathbf{M} = M\hat{x}$ changes to $\mathbf{M} = -M\hat{x}$. The difference of the two voltage drops is proportional to R_2. This is the signature of R_2. To obtained R_3, one can measure the tunneling resistances for $\mathbf{M} = \pm M\hat{z}$. The difference of the two tunneling resistances is proportional to $R_2 + R_3 - R_4$.

The new galvanomagnetic effects reported here come from the two dimensional nature of films. The interfacial effects are not new in physics [24–26] and exist in both magnetic and non-magnetic systems. Our general analysis points out that the new galvanomagnetic effects should exist in a polycrystalline magnetic film although it reveals neither microscopic origins of these effects nor their possible magnitudes. To utilize these new effects as material probes or to search for materials with larger effects, one needs to understand how microscopic interactions generate these new effects. Another interesting problem is to generalize the analysis to crystalline materials because it can help us to understand those electron transport measurements on magnetic single crystals. Since a crystal can provide intrinsic crystal vectors or tensors, $\overleftrightarrow{\rho}(\mathbf{M}, \hat{x}_1, \hat{x}_2, ...)$ shall depend not only on $\mathbf{M}$, but also on other tensors or vectors $(\hat{x}_1, \hat{x}_2, ...)$ that a crystal possess. Then, one needs to construct all possible vectors and traceless symmetric tensors out of these available variables in order to find out all possible galvanomagnetic effects.

Clearly, all three new terms involve the coupling between the magnetization and charge current so that they can generate dc-voltage in the electrical detection of FMR just like what AMR and EHE do [16, 18–20]. The electrical detection of FMR has been used in recent years to extract spin pumping and the spin Hall angle that measures the strength of both spin Hall effect and the inverse spin Hall effect [16, 18–20]. Obviously, the new galvanomagnetic effect should have important implications on reliability of extracting material parameters like the spin Hall angle of various metals since most experiments used polycrystalline magnetic films.

In conclusion, we present a general analysis of the linear response of polycrystalline magnetic films and predict three new galvanomagnetic effects. The longitudinal resistivity contains, in general, a term linear in the magnetization component perpendicular to a film. A current along the magnetization can induce an electric field perpendicular to a film. Furthermore, a current perpendicular to a film can induce an electric field along the magnetization direction. Their implications are discussed. The typical features of these effects are analyzed and possible ways to experimentally verify them are suggested.

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* Electronic address: phxwan@ust.hk

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